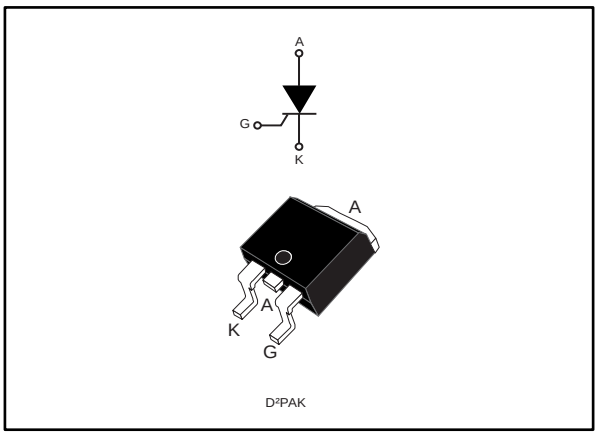
TN5015H-6G

High temperature 50 A SCRs

Datasheet - production data



Features

- High junction temperature: T_j = 150 °C
- High noise immunity dV/dt = 500 V/µs up to 150 °C
- Gate triggering current I_{GT} = 15 mA
- Peak off-state voltage V_{DRM}/V_{RRM} = 600 V
- High turn-on current rise dI/dt = 100 A/µs
- ECOPACK®2 compliant component

Applications

- Motorbike voltage regulator circuits
- Inrush current limiting circuits
- Motor control circuits and starters
- Solid state relays

Description

Thanks to its junction temperature T_j up to 150 °C, the device offers high thermal performance operation up to 50 A. Its D²PAK package allows modern SMD designs as well as compact back to back configuration.

Its trade-off noise immunity (dV/dt = 500 V/µs) versus its gate triggering current (I_{GT} = 15 mA) and its turn-on current rise (dI/dt = 100 A/µs) allow to design robust and compact control circuit for voltage regulator in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances, inrush current limiting circuits.

Table 1: Device summary

Order code	Package	V_{DRM}/V_{RRM}	I_{GT}
TN5015H-6G	D²PAK	600 V	15 mA

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		T_c = 120 °C	50	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)		T_c = 122 °C	30	A
			T_c = 128 °C	25	
			T_c = 134 °C	20	
I_{TSM}	Non repetitive surge peak on-state current		t_p = 8.3 ms	493	A
			t_p = 10 ms	450	
I^2t	I^2t value for fusing		t_p = 10 ms	1012	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT}, tr ≤ 100 ns		f = 60 Hz	100	A/µs
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage		T_j = 150 °C	600	V
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage		t_p = 10 ms	V_{DRM}/V_{RRM} + 100	V
I_{GM}	Peak gate current	t_p = 20 µs	T_j = 150 °C	4	A
$P_{G(AV)}$	Average gate power dissipation		T_j = 150 °C	1	W
V_{RGM}	Maximum peak reverse gate voltage			5	V
T_{stg}	Storage junction temperature range			-40 to +150	°C
T_j	Maximum operating junction temperature			-40 to +150	°C

Table 3: Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions			Value	Unit
I_{GT}	V_D = 12 V, R_L = 33 Ω		Max.	15	mA
V_{GT}			Max.	1.3	V
V_{GD}	V_D = V_{DRM}, R_L = 3.3 kΩ	T_j = 150 °C	Min.	0.15	V
I_H	I_T = 500 mA, gate open		Max.	60	mA
I_L	I_G = 1.2 x I_{GT}		Max.	80	mA
dV/dt	V_D = 402 V, gate open	T_j = 150 °C	Min.	500	V/µs
t_{gt}	I_{TM} = 100 A, V_D = 600 V, I_G = 100 mA, (dI_G/dt) max = 0.2 A/µs		Typ.	1.9	µs
t_q	I_{TM} = 100 A, V_D = 402 V, (d_I/dt)off = 30 A/µs, V_R = 25 V, dV_D/dt = 50 V/µs	T_j = 150 °C	Typ.	85	µs

ITable 4: Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	I_{TM} = 100 A, t_p = 380 µs	T_j = 25 °C	Max.	1.65	V
V_{TO}	Threshold voltage	T_j = 150 °C	Max.	0.85	
R_D	Dynamic resistance	T_j = 150 °C	Max.	9	mΩ
I_{DRM}, I_{RRM}	V_D = V_{DRM} = V_{RRM}	T_j = 25 °C	Max.	10	µA
		T_j = 150 °C		6	mA

Table 5: Thermal parameters

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case (DC)		Max.	0.6	°C/W
$R_{th(j-a)}$	Junction to ambient (DC)	S(1) = 1 cm²	Typ.	45	

Notes:

(1)S = Copper surface under tab

1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current

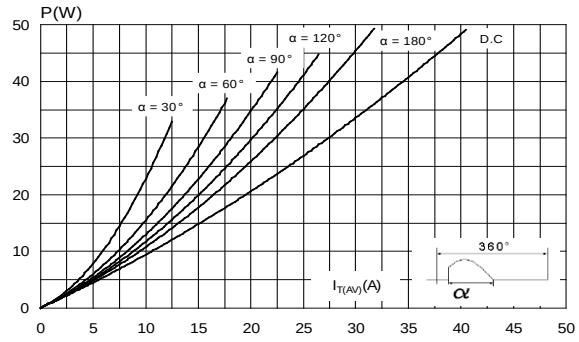


Figure 2: Average and DC on-state current versus case temperature

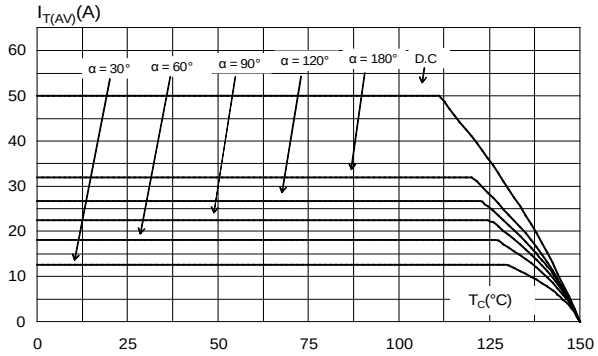


Figure 3: Average and D.C. on state current versus ambient temperature

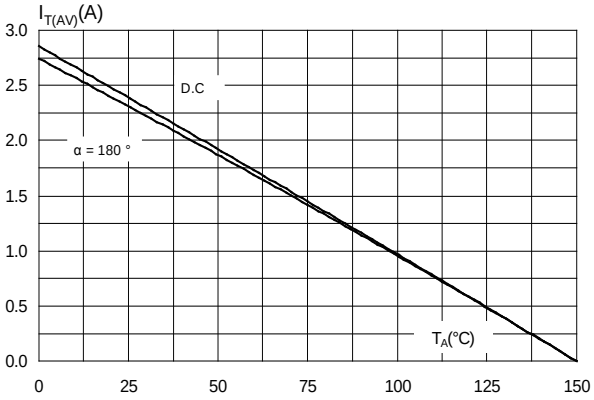


Figure 4: Relative variation of thermal impedance versus pulse duration

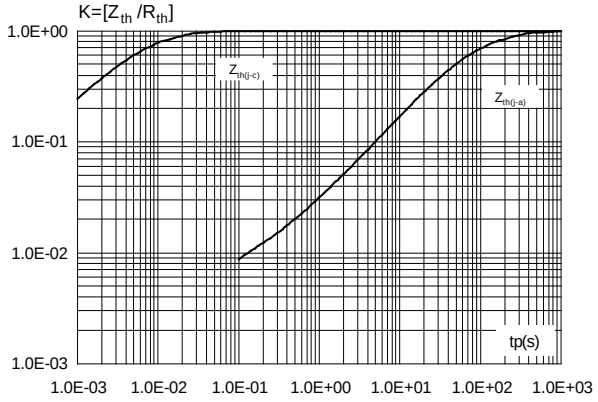


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

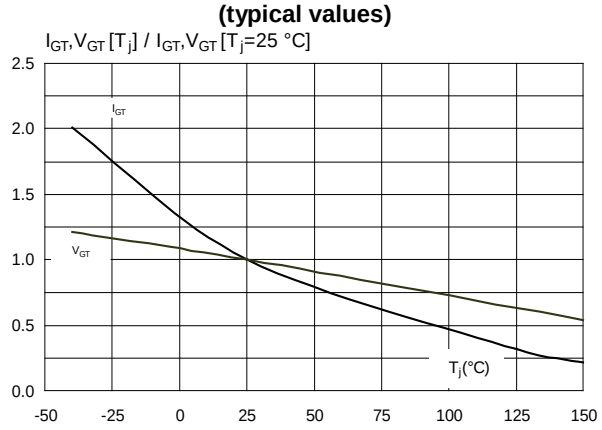


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)

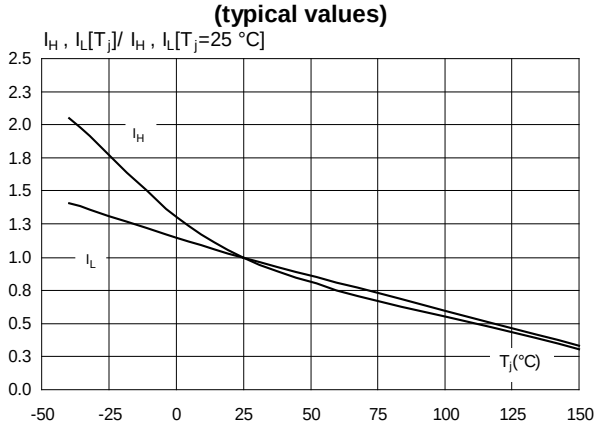


Figure 7: Relative variation of static dV/dt immunity versus junction temperature (typical values)

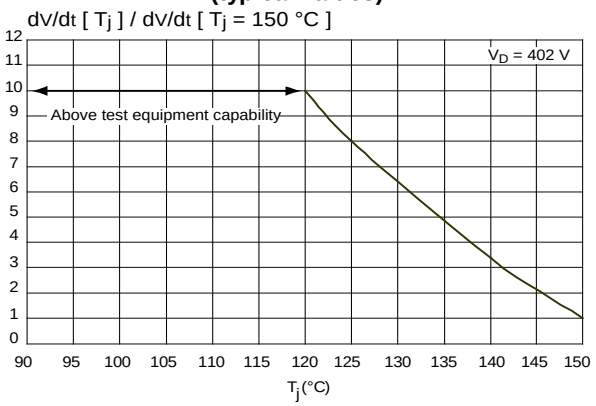


Figure 8: Surge peak on-state current versus number of cycles

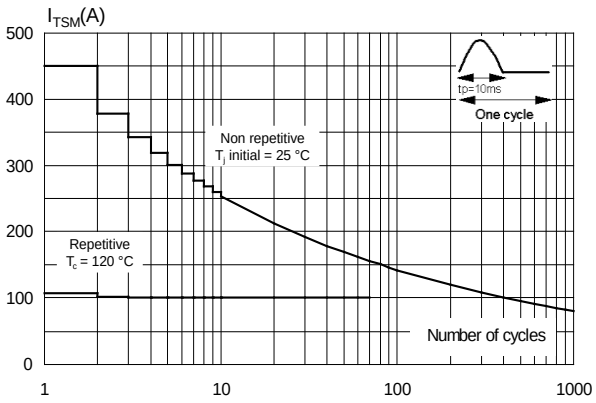


Figure 9: Non repetitive surge peak on-state current for a sinusoidal pulse with width t_p < 10 ms

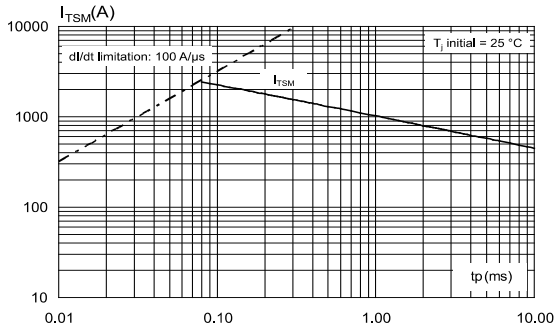


Figure 10: On-state characteristics (maximum values)

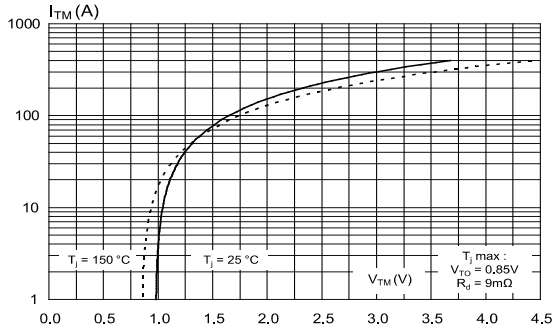


Figure 11: Relative variation of leakage current versus junction temperature

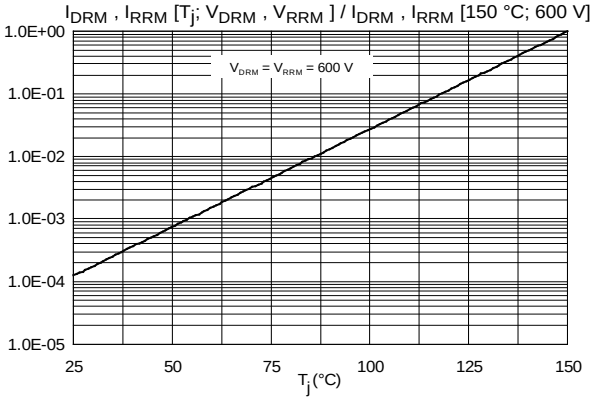
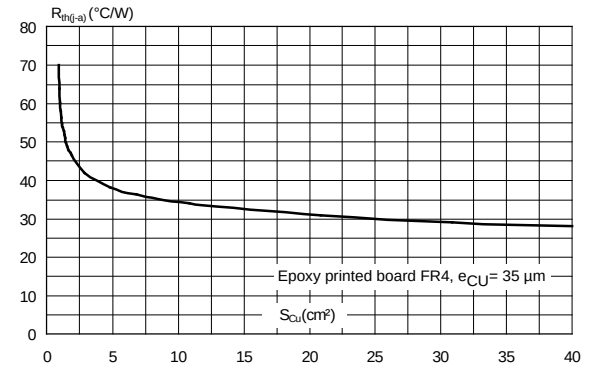


Figure 12: Thermal resistance junction to ambient versus copper surface under tab



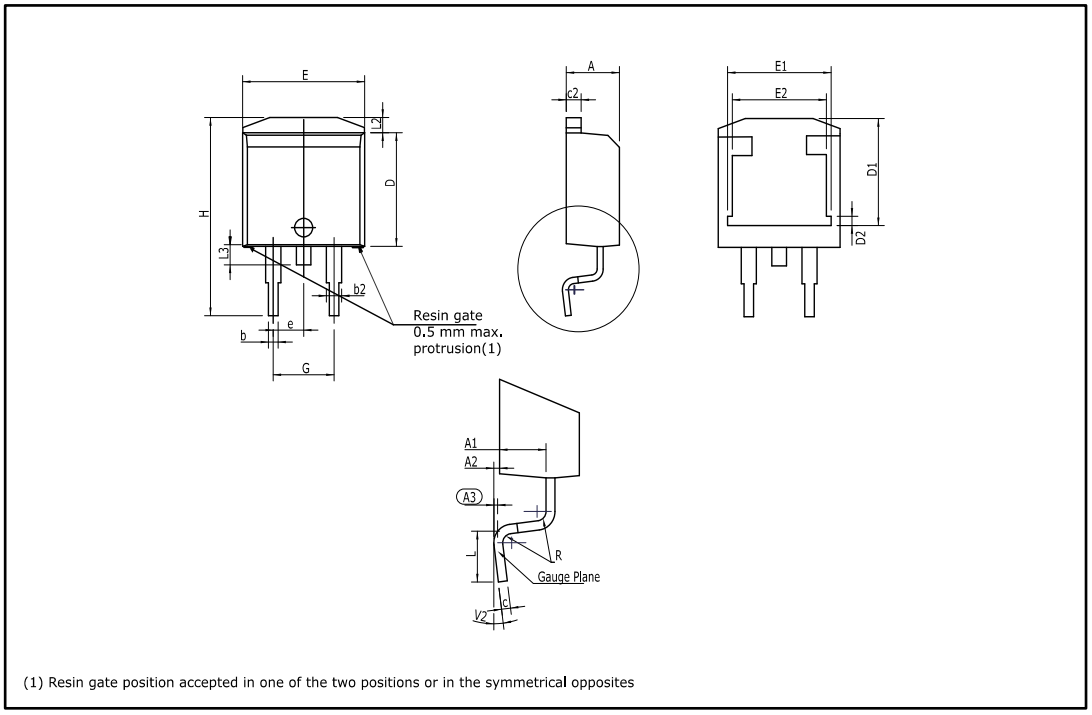
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 D²PAK package information

Figure 13: D²PAK package outline



(1) Resin gate position accepted in one of the two positions or in the symmetrical opposites

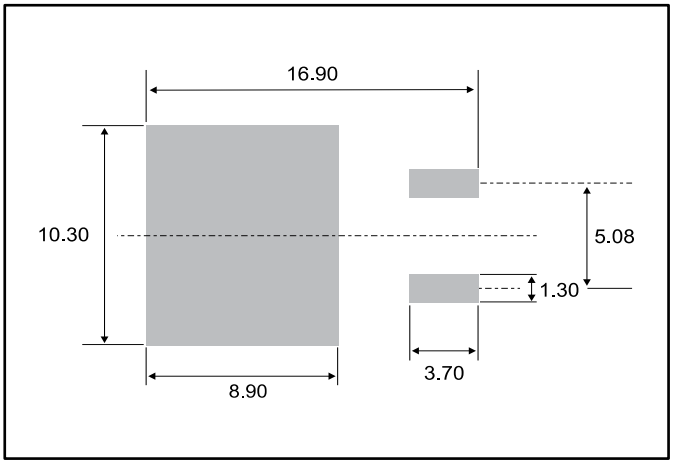
Table 6: D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e	2.54			0.1		
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.27		1.40	0.0500		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

Notes:

[1]Dimensions in inches are given for reference only

Figure 14: D²PAK recommended footprint (dimensions are in mm)



3 Ordering information

Figure 15: Ordering information scheme

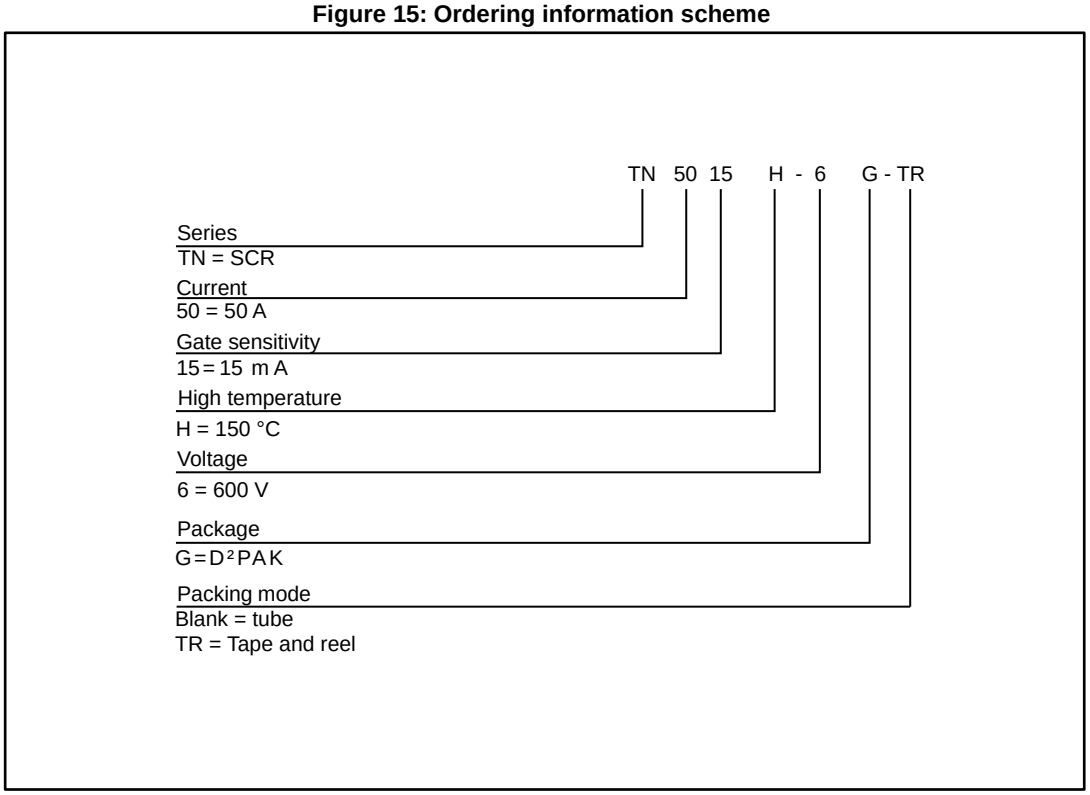


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN5015H-6G	TN5015H6	D²PAK	1.5 g	50	Tube
TN5015H-6G-TR	TN5015H6	D²PAK	1.5 g	1000	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
08-Jun-2017	1	Initial release.

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